



2:1 MIPI D-PHY and C-PHY Switch

Features

- → SPDT (10x) Switch Type and Signal Type Support D-PHY and C-PHY
- → Data Rate: D-PHY(2.5Gbps) 4-Data Lane and C-PHY (2.5Gsps) 3-Data Lane
- → Supports 2:1 Clock Differential Signal
- → -3dB Bandwidth: 4.5GHz Typical
- → Low Crosstalk: -30dB @ 1.25GHz
- → Low Off Isolation: -26dB @ 1.25GHz
- → Input Signals 0 to 1.3V
- → Ron: 6Ω Typical LP & HS MIPI
- → Δ R_{ON}: 0.1Ω Typical LP & HS MIPI
- → R_{ON_FLAT}: 0.3Ω Typical LP & HS MIPI
- → I_{CCZ}: 1µA Maximum
- → I_{CC}: 15µA Typical
- → C_{ON}: 1.5pF Typical
- → Skew of Opposite Transitions of the Same Output: 2ps Typical
- → V_{DD} Operating Range: 1.5V to 5V
- → ESD Tolerance: 2kV HBM
- → Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- → Halogen and Antimony Free. "Green" Device (Note 3)
- → For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- → Packaging (Pb-free & Green): 36-Pin, CSP (GE) 2.44 × 2.44

Description

Diodes' PI3WVR646 is a 4-data lane D-PHY or 3-data lane C-PHY MIPI switch. This 10-channel single-pole, double-throw (SPDT) switch is optimized for switching between high-speed (HS) or low-power (LP) MIPI signal. The PI3WVR646 is designed for the MIPI specification and allows connection to a CSI or DSI module.

Applications

- → Cellular Phones, Smart Phones
- → Tablets
- → Laptops
- → Displays

Notes:

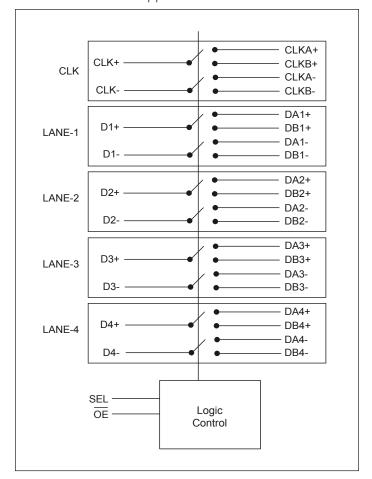
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



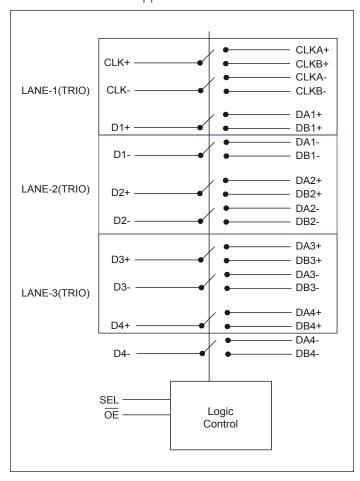


Block Diagram

PI3WVR646 D-PHY Application



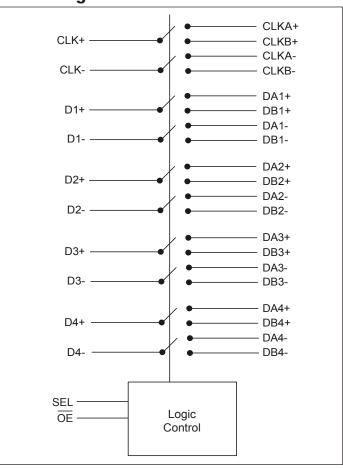
PI3WVR646 C-PHY Application







Block Diagram



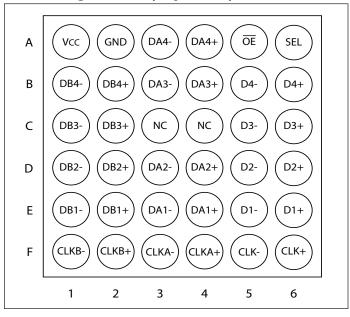
Truth Table

| SEL | OE Function | |
|------|---------------|--|
| LOW | LOW | $CLK+ = CLKA+, CLK- = CLKA-, Dn(\pm) = DAn(\pm)$ |
| HIGH | LOW | $CLK+ = CLKB+, CLK- = CLKB-, Dn(\pm) = DBn(\pm)$ |
| X | HIGH | Clock and Data Ports High Impedance |





Pin Configuration (Top View)



Pin Description

| Pin# | Pin Name | Type | Description |
|--------|-----------------|--------|--|
| A1 | V _{CC} | Power | 1.5V to 5V power supply |
| A2 | GND | Ground | Ground |
| A3 | DA4- | I/O | Negative differential signal 4 for port A |
| A4 | DA4+ | I/O | Positive differential signal 4 for port A |
| A5 | ŌĒ | I | Output enable. If \overline{OE} is low, IC enables. If \overline{OE} is high, IC powers down. All I/Os are Hi-Z. |
| A6 | SEL | I/O | Switch logic control |
| B1 | DB4- | I/O | Negative differential signal 4 for port B |
| B2 | DB4+ | I/O | Positive differential signal 4 for port B |
| В3 | DA3- | I/O | Negative differential signal 3 for port A |
| B4 | DA3+ | I/O | Positive differential signal 3 for port A |
| B5 | D4- | I/O | Negative differential signal 4 for COM port |
| В6 | D4+ | I/O | Positive differential signal 4 for COM port |
| C1 | DB3- | I/O | Negative differential signal 3 for port B |
| C2 | DB3+ | I/O | Positive differential signal 3 for port B |
| C3, C4 | NC | _ | Not connected |
| C5 | D3- | I/O | Negative differential signal 3 for COM port |
| C6 | D3+ | I/O | Positive differential signal 3 for COM port |
| D1 | DB2- | I/O | Negative differential signal 2 for port B |

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Pin Description Cont.

| Pin# | Pin Name | Type | Description |
|------|----------|------|---|
| D2 | DB2+ | I/O | Positive differential signal 2 for port B |
| D3 | DA2- | I/O | Negative differential signal 2 for port A |
| D4 | DA2+ | I/O | Positive differential signal 2 for port A |
| D5 | D2- | I/O | Negative differential signal 2 for COM port |
| D6 | D2+ | I/O | Positive differential signal 2 for COM port |
| E1 | DB1- | I/O | Negative differential signal 1 for port B |
| E2 | DB1+ | I/O | Positive differential signal 1 for port B |
| E3 | DA1- | I/O | Negative differential signal 1 for port A |
| E4 | DA1+ | I/O | Positive differential signal 1 for port A |
| E5 | D1- | I/O | Negative differential signal 1 for COM port |
| E6 | D1+ | I/O | Positive differential signal 1 for COM port |
| F1 | CLKB- | I/O | Clock negative differential signal for port B |
| F2 | CLKB+ | I/O | Clock positive differential signal for port B |
| F3 | CLKA- | I/O | Clock negative differential signal for port A |
| F4 | CLKA+ | I/O | Clock positive differential signal for port A |
| F5 | CLK- | I/O | Clock negative differential signal for COM port |
| F6 | CLK+ | I/O | Clock positive differential signal for COM port |

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Absolute Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

| | , |
|--|-------------------------|
| V _{CC} , Supply Voltage, | 0.5V to 6.0V |
| V _{CNTRL} , DC Input Voltage (OE, SEL) ⁽¹⁾ | 0.5V to V _{CC} |
| V _{SW} , DC Switch I/O Voltage ^(1,2) | 0.3V to 4.0V |
| I _{IK} , DC Input Diodes Current | 50mA |
| I _{OUT} , DC Output Current | 25mA |
| T _{STG} , Storage Temperature | 65°C to +150°C |
| Tj, Junction Temperature | 125°C |
| ESD: | |
| Human Body Model, JEDEC: JESD22-A114, All Pins | 2.0kV |
| Charged Device Model, JEDEC: JESD22-C101 | 1.0kV |

Note:

Stresses greater than those listed under MAXIMUM RAT-INGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Note:

- 1. The input and output negative ratings can be exceeded if the input and output diode current ratings are observed.
- 2. V_{SW} refers to analog data switch paths.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications.

| Symbol | Description | Test Conditions | Min. | Max. | Units |
|--------------------|--|------------------------|------|-----------------|-------|
| V _{CC} | Supply Voltage | _ | 1.5 | 5.0 | V |
| V _{CNTRL} | Control Input Voltage (SEL, \overline{OE}) ⁽¹⁾ | _ | 0 | V _{CC} | V |
| V _{SW} | Control 110 Valence (CLV D. CLVA CLVD DA DD.) | - HS Mode | 0 | 0.5 | V |
| | Switch I/O Voltage (CLK-, D-, CLKA-, CLKB-, DA-, DB-) | - LP Mode | 0 | 1.3 | V |
| T _A | Operating Temperature | _ | -40 | +85 | °C |

Note:

DC and Transient Characteristics

All typical values are at $T_{\Delta} = 25^{\circ}\text{C}$ unless otherwise specified.

| | | | | $T_A = -40^{\circ}\text{C to} +85^{\circ}\text{C}$ | | | |
|---|---|----------------------------------|---------------------|--|------|------|-------|
| Symbol | Description | Test Conditions | V _{CC} (V) | Min. | Тур. | Max. | Units |
| V _{IK} | Clamp Diode Voltage (OE, SEL) | $I_{IN} = -18mA$ | 1.5 | -1.2 | _ | -0.6 | V |
| V_{IH} | Input Voltage High | SEL, OE | 1.5 to 5 | 1.3 | _ | _ | V |
| $V_{\rm IL}$ | Input Voltage Low | SEL, OE | 1.5 to 5 | _ | _ | 0.5 | V |
| I _{IN} | Control Input Leakage (OE, SEL) | $V_{CNTRL} = 0$ to V_{CC} | 5 | -0.5 | | 0.5 | μΑ |
| I _{NO(OFF)} I _{NC(OFF)} | Off Leakage Current of Port CLKA-, DA-, CLKB- and DB- | $V_{SW} = 0.0 \le DATA \le 1.3V$ | 5 | -0.5 | _ | 0.5 | μА |
| I _{A(ON)} | On Leakage Current of Common Ports (CLK-, D-) | $V_{SW} = 0.0 \le DATA \le 1.3V$ | 5 | -0.5 | _ | 0.5 | μА |

^{1.} The control inputs must be held HIGH or LOW; they must not float.





DC and Transient Characteristics Cont.

| | | | | $T_A = -40^{\circ} \text{C to } +85^{\circ} \text{C}$ | | | |
|---------------------------|---|--|---------------------|---|------|------|----------|
| Symbol | Description | Test Conditions | V _{CC} (V) | Min. | Тур. | Max. | Units |
| I _{OFF} | Power-Off Leakage Current (All I/O Ports) | $V_{SW} = 0.0 \text{ or } 1.3V$ | 0 | -0.5 | _ | 0.5 | μА |
| I_{OZ} | Off-State Leakage | $\frac{V_{SW} = 0.0 \le DATA \le 1.3V,}{OE = High}$ | 5 | -0.5 | _ | 0.5 | μА |
| | | | 1.5 | | | | |
| R _{ON_MIPI_HS} | Switch On Resistance for HS MIPI | $I_{ON} = -8mA$, $OE = 0V$, $SEL = V_{CC}$ or $0V$, $CLKA$, | 2.5 | _ | 6 | 9 | Ω |
| TON_MIPI_HS | owiten on resistance for 110 1/111 1 | CLKB, DB- or DA- = $0.2V$ | 3.3 | | | | <u> </u> |
| | | | 5 | | | | |
| | | $I_{ON} = -8mA, \overline{OE} = 0V,$ | 1.5 | | | | |
| R _{ON_MIPI_LP} | Switch On Resistance for LP MIPI | $SEL = V_{CC}$ or $0V$, $CLKA$, | 2.5 | _ | 6 | 9 | Ω |
| | | CLKB, DB- or DA- = 1.2V | 3.3 | _ | | | |
| | | | 5 | | | | |
| | On Resistance Matching Between HS MIPI Channels ⁽¹⁾ | $I_{ON} = -8mA, \overline{OE} = 0V,$ $SEL = V_{CC} \text{ or } 0V, CLKA,$ CLKB, DB- or DA- = 0.2V | 2.5 | | 0.1 | _ | |
| $\Delta R_{ON_MIPI_HS}$ | | | 3.3 | _ | | | Ω |
| | | | 5 | | | | |
| | On Resistance Matching Between LP MIPI Channels ⁽¹⁾ | $I_{ON} = -8mA, \overline{OE} = 0V,$ $SEL = V_{CC} \text{ or } 0V,$ $CLKA, CLKB,$ $DB- \text{ or } DA- = 1.2V$ | 1.5 | | 0.1 | _ | |
| | | | 2.5 | _ | | | |
| $\Delta R_{ON_MIPI_LP}$ | | | 3.3 | | | | Ω |
| | | | 5 | | | | |
| | O. D | $I_{ON} = -8mA$, $\overline{OE} = 0V$, $SEL = V_{CC}$ or $0V$, $CLKA$, CLKB, DB - or DA - = 0 to | 1.5 | | 0.3 | | |
| R _{ON_FLAT_} | | | 2.5 | | | | Ω |
| MIPI_HS | On Resistance Flatness for HS MIPI | | 3.3 | _ | 0.5 | _ | 2.2 |
| | | 0.3V | 5 | | | | |
| | | $I_{ON} = -8 \text{mA}, \overline{OE} = 0 \text{V},$ | 1.5 | | | | |
| $R_{ON_FLAT_}$ | On Resistance Flatness for LP MIPI | $SEL = V_{CC}$ or $0V$, $CLKA$, | 2.5 | | 0.3 | _ | Ω |
| MIPI_LP | | CLKB, DB- or DA- = 0 to $1.3V$ | 3.3 | | 0.3 | | |
| | | V 0 V I 0 | 5 | | | | |
| I _{CC} | Quiescent Supply Current | $\frac{V_{SEL} = 0 \text{ or } V_{CC}, I_{OUT} = 0,}{OE = 0V}$ | 5 | _ | 15 | 30 | μA |
| I_{CCZ} | Quiescent Supply Current (High Impedance) | $\frac{V_{SEL}}{OE} = 0$ or V_{CC} , $I_{OUT} = 0$, | 5 | _ | _ | 1 | μА |
| I_{CCT} | Increase in I_{CC} Current Per Control Voltage and V_{CC} | $\frac{V_{SEL} = 0 \text{ or } V_{CC},}{OE = 1.5V}$ | 5 | _ | 1 | _ | μА |





AC Electrical Characteristics

All typical values are for $V_{CC} = 3.3V$ and $T_A = 25^{\circ}C$ unless otherwise specified.

| | | | | $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$ | | | |
|-------------------|--|---|---------------------|---|------|------|-------|
| Symbol | Description | Test Conditions | V _{CC} (V) | Min. | Тур. | Max. | Units |
| t _{INIT} | Initialization Time V_{CC} to $Output^{(1)}$ | $R_L = 50\Omega, C_L = 0pF,$ $V_{SW} = 0.6V$ | 1.5 to 5 | _ | 60 | _ | μs |
| $t_{\rm EN}$ | Enable Time OE to Output | $R_L = 50\Omega, C_L = 0pF,$ $V_{SW} = 0.6V$ | 1.5 to 5 | _ | 60 | 150 | μs |
| $t_{ m DIS}$ | Disable Time OE to Output | $R_L = 50\Omega, C_L = 0pF,$ $V_{SW} = 0.6V$ | 1.5 to 5 | _ | 35 | 250 | ns |
| t _{ON} | Turn-On Time SEL to Output | $R_{L} = 50\Omega, C_{L} = 0pF,$ $V_{SW} = 0.6V$ | 1.5 to 5 | _ | 350 | 1100 | ns |
| t _{OFF} | Turn-Off Time SEL to Output | $R_{L} = 50\Omega, C_{L} = 0pF,$ $V_{SW} = 0.6V$ | 1.5 to 5 | _ | 125 | 800 | ns |
| $t_{ m BBM}$ | Break-Before-Make Time | $R_{L} = 50\Omega, C_{L} = 0pF,$ $V_{SW} = 0.6V$ | 1.5 to 5 | _ | _ | 450 | ns |
| t_{PD} | Propagation Delay ⁽¹⁾ | $C_L = 0$ pF, $R_L = 50$ Ω | 1.5 to 5 | _ | _ | 0.25 | ns |
| O _{IRR} | Off Isolation for MIPI ⁽¹⁾ | $\begin{aligned} &R_L = 50\Omega, f = 1250 MHz, \\ &\overline{OE} = HIGH, \\ &V_{SW} = 0.2 V_{PP} \end{aligned}$ | 1.5 to 5 | _ | -26 | _ | dB |
| X_{TALK} | Crosstalk for MIPI ⁽¹⁾ | $R_{L} = 50\Omega, f = 1250 MHz,$ $SEL = HIGH,$ $V_{SW} = 0.2 V_{PP}$ | 1.5 to 5 | _ | _ | -30 | dB |
| | | $R_{L} = 50\Omega, f = 1250 MHz,$ $SEL = LOW, V_{SW} = 0.2 V_{PP}$ | | _ | _ | -30 | |
| T | Insertion Locally | $R_L = 50\Omega, C_L = 0pF,$ $f = 1250MHz,$ $V_{SW} = 0.2V_{PP}$ | 1.5 to 5 | _ | -0.9 | _ | J.D. |
| I_{LOSS} | Insertion Loss ⁽¹⁾ | $R_{L} = 50\Omega, C_{L} = 0pF,$ f = 750MHz, $V_{SW} = 0.2V_{PP}$ | 1.5 to 5 | _ | -0.7 | _ | dB |
| BW | -3db Bandwidth ⁽¹⁾ | $R_{L} = 50\Omega, C_{L} = 0pF,$ $V_{SW} = 0.2V_{PP}$ | 1.5 to 5 | 3.0 | 4.5 | _ | GHz |

Note:

1. Guaranteed by characterization.





High-Speed-Related AC Electrical Characteristics

| | | | | $T_A = -$ | 40°C to | +85°C | | |
|--------------------|---|--|---------------------|-----------|---------|-------|-------|--|
| Symbol | Description | Test Conditions | V _{CC} (V) | Min. | Тур. | Max. | Units | |
| t _{SK(P)} | HS Mode Skew of Opposite Transitions of the Same Output ⁽¹⁾ | $R_{L} = 50\Omega, C_{L} = 0pF,$ $V_{SW} = 0.3V$ | 1.5 to 5 | _ | 2 | 4 | ps | |
| | HS Mode Slew of all Group A or Group B Channels ⁽¹⁾ | $R_L = 50\Omega, C_L = 0pF,$ $V_{SW} = 0.3V$ | 1.5 to 5 | _ | 4 | 7 | | |

Note:

Capacitance

| | | | $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$ | | +85°C | |
|------------------|----------------------------------|---|---|------|-------|-------|
| Symbol | Description | Test Conditions | Min. | Тур. | Max. | Units |
| $C_{\rm IN}$ | Control Pin Input Capacitance(1) | $V_{CC} = 0V, f = 1MHz$ | _ | 2.1 | _ | pF |
| C _{ON} | On Capacitance ⁽¹⁾ | $V_{CC} = 3.3V$, $\overline{OE} = 0V$, $f = 1250MHz$ (in HS common value) | _ | 1.5 | _ | pF |
| C _{OFF} | Off Capacitance ⁽¹⁾ | V_{CC} or \overline{OE} = 3.3V, f = 1250MHz (both sides in HS common value) | _ | 0.9 | _ | pF |

Note:

^{1.} Guaranteed by characterization.

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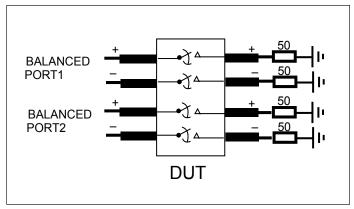


Fig 1. Crosstalk Setup

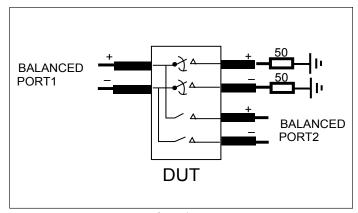


Fig 2. Off-Isolation Setup

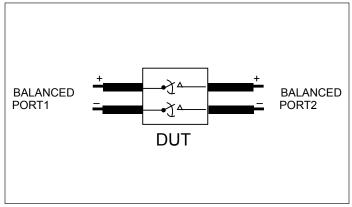
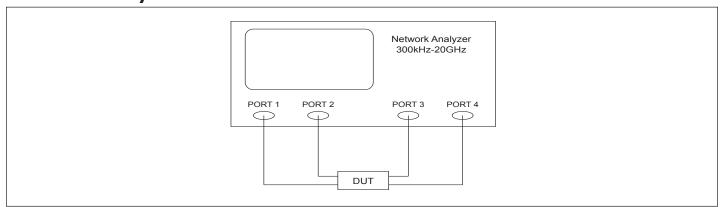


Fig 3. Differential Insertion Loss

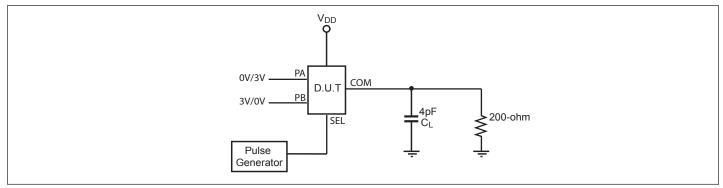
Test Circuit for Dynamic Electrical Characteristics







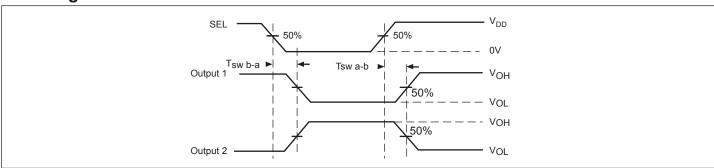
Test Circuit for Electrical Characteristics(1-4)



Notes:

- 1. C_L = Load capacitance: includes jig and probe capacitance.
- 2. R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator.
- 3. All input impulses are supplied by generators having the following characteristics: $PRR \leq MHz, Z_O = 50\Omega, t_R \leq 2.5ns, t_F \leq 2.5ns$
- 4. The outputs are measured one at a time with one transition per measurement.

Switching Waveforms



Voltage Waveforms for Select Timing

Test Condition

| Output 1 Test Condition | Output 2 Test Condition |
|-------------------------|-------------------------|
| PA = Low | PA = High |
| PB = High | PB = Low |

Part Marking

CSP Package



Z: Die Rev YY: Year

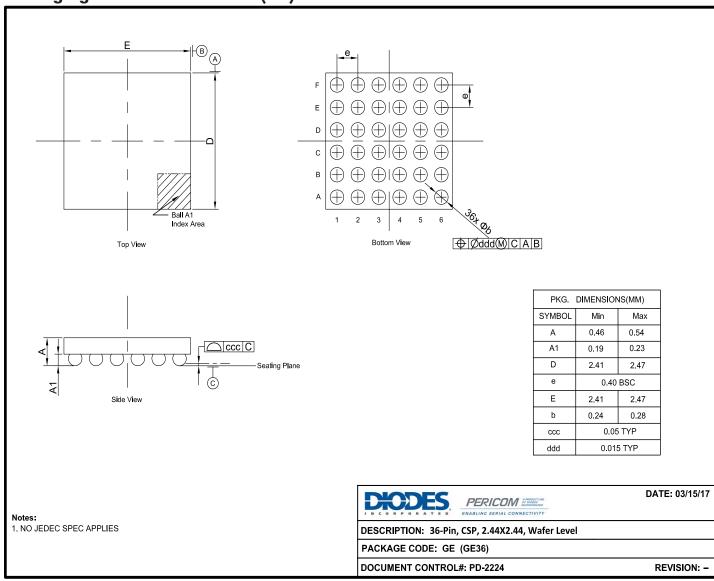
WW: Workweek

1st X: Assembly Site Code 2nd X: Fab Site Code





Packaging Mechanical: 36-CSP (GE)



For latest package information:

 $See \ http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/.$

Ordering Information

| Ordering Code | Package Code | Package Description |
|---------------|--------------|--------------------------------------|
| PI3WVR646GEEX | GE | 36-Pin, 2.44×2.44, Wafer Level (CSP) |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. E = Pb-free and Green
- 5. X suffix = Tape/Reel





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PI5A3166TAEX XS3A1T3157GMX TC4066BP(N,F) DG302BDJ-E3 PI5A100QEX HV2301FG-G RS2117YUTQK10 RS2118YUTQK10

RS22227XUTQK10 ADG452BRZ-REEL7 MAX391CPE+ MAX4730EXT+T MAX314CPE+ BU4066BCFV-E2 MAX313CPE+

BU4S66G2-TR NLASB3157MTR2G TS3A4751PWR NLAST4599DFT2G NLAST4599DTT1G DG419LDY+T DG300BDJ-E3

DG2503DB-T2-GE1 TC4W53FU(TE12L,F) DG3257DN-T1-GE4 ADG1611BRUZ-REEL7 LTC201ACN#PBF 74LV4066DB,118

ISL43410IUZ FSA2275AUMX DIO1500WL12 ADG742BKSZ-REEL7 DIO1269LP10 DG201HSDJ-E3 DG307BDJ-E3